

Polar™ Power MOSFET

HiPerFET™

IXFB52N90P

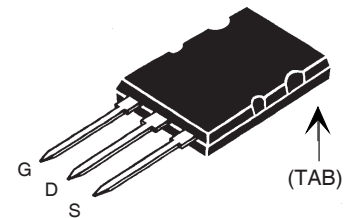
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$V_{DSS} = 900V$
 $I_{D25} = 52A$
 $R_{DS(on)} \leq 160m\Omega$
 $t_{rr} \leq 300ns$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	900	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	900	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	52	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	104	A
I_A	$T_C = 25^\circ C$	26	A
E_{AS}	$T_C = 25^\circ C$	2	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	20	V/ns
P_D	$T_C = 25^\circ C$	1250	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
F_C	Mounting Force	30..120/6.7..27	N/lb.
Weight		10	g

PLUS264™



G = Gate D = Drain
S = Source TAB = Drain

Features

- Fast Intrinsic Diode
- Avalanche Rated
- Low Package Inductance

Advantages

- Plus 264™ Package for Clip or Spring Mounting
- Space Savings
- High Power Density

Applications

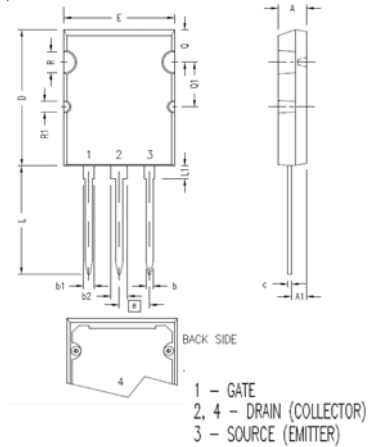
- Switched-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 3mA$	900		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1mA$	3.5		6.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			50 μA 4 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			160 m Ω

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20V, I_D = 0.5 \cdot I_{D25}$, Note 1	20	35	S
R_{Gi}	Gate Input Resistance		1.56	Ω
C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		19	nF
C_{oss}			1180	pF
C_{rss}			24	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		63	ns
t_r			80	ns
$t_{d(off)}$			95	ns
t_f			42	ns
$Q_{g(on)}$	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		308	nC
Q_{gs}			117	nC
Q_{gd}			132	nC
R_{thJC}			0.10	$^{\circ}C/W$
R_{thCS}		0.13		$^{\circ}C/W$

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0V$			52 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			208 A
V_{SD}	$I_F = I_S, V_{GS} = 0V$, Note 1			1.5 V
t_{rr}	$I_F = 26A, -di/dt = 100A/\mu s$ $V_R = 100V$			300 ns
Q_{RM}			1.8	μC
I_{RM}			26	A

PLUS264™ (IXFB) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36

Note 1: Pulse Test, $t \leq 300\mu s$; Duty Cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

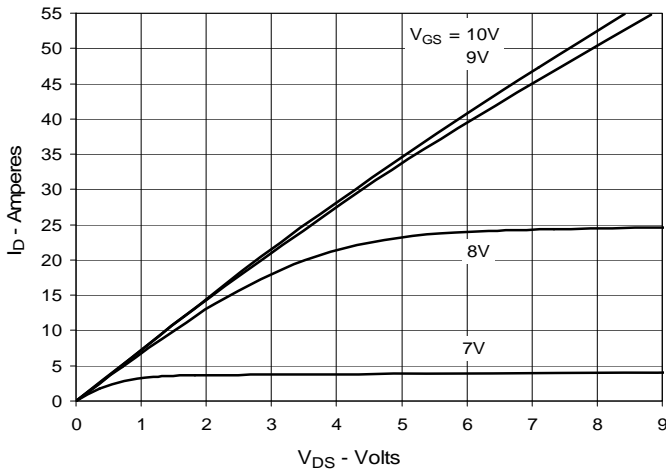
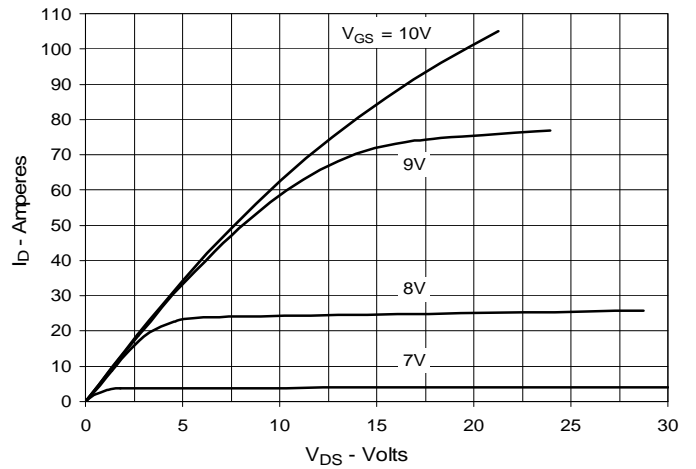
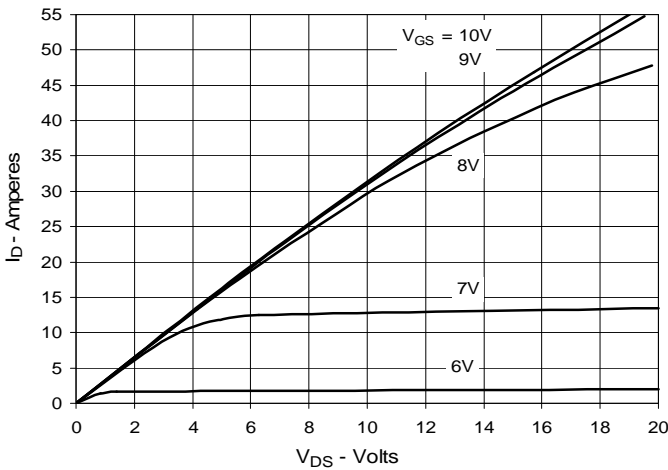
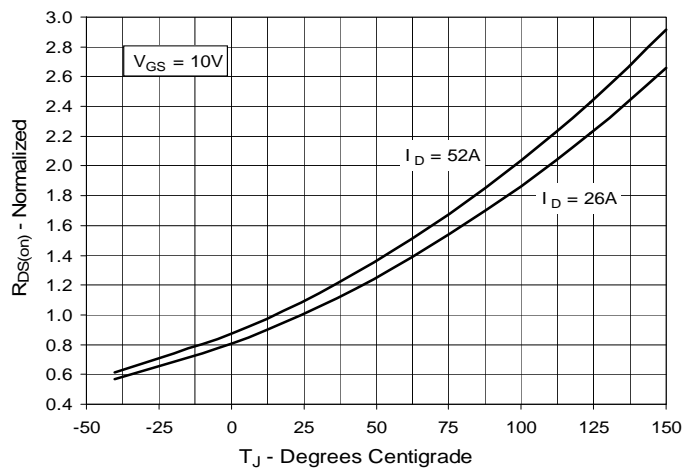
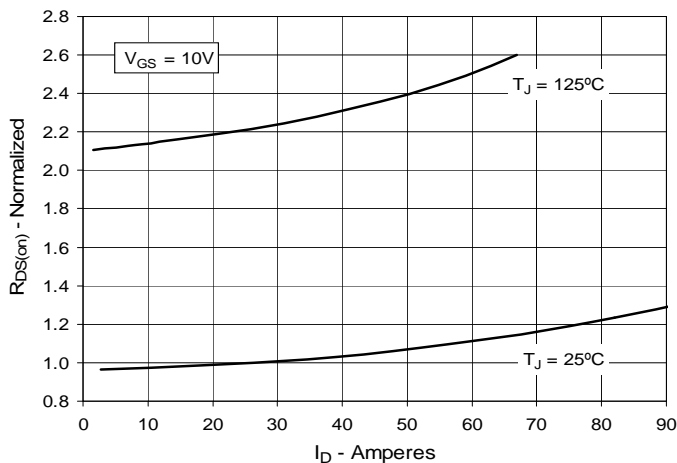
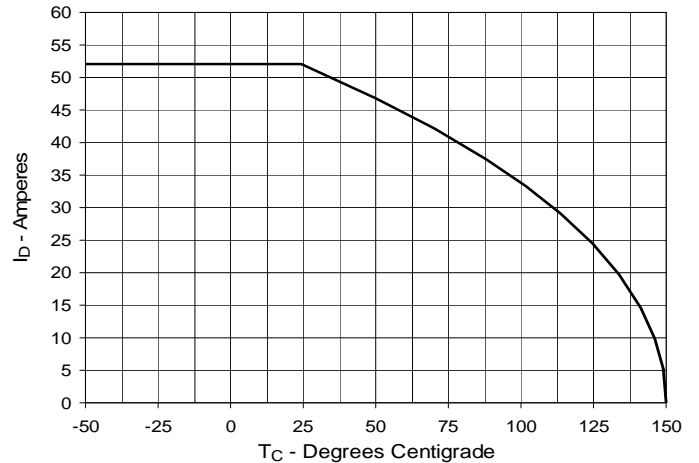
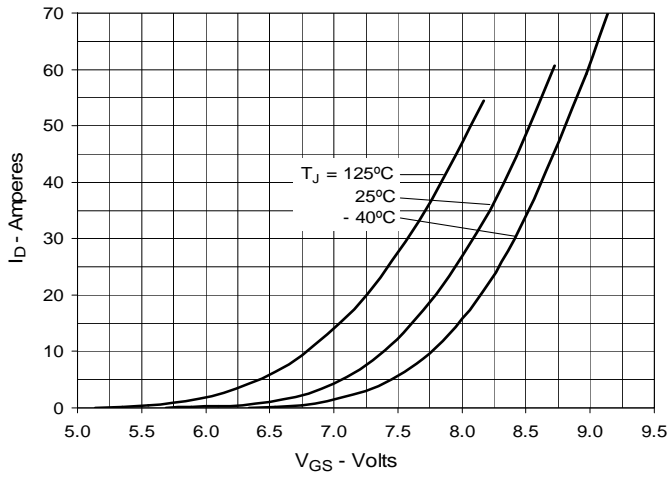
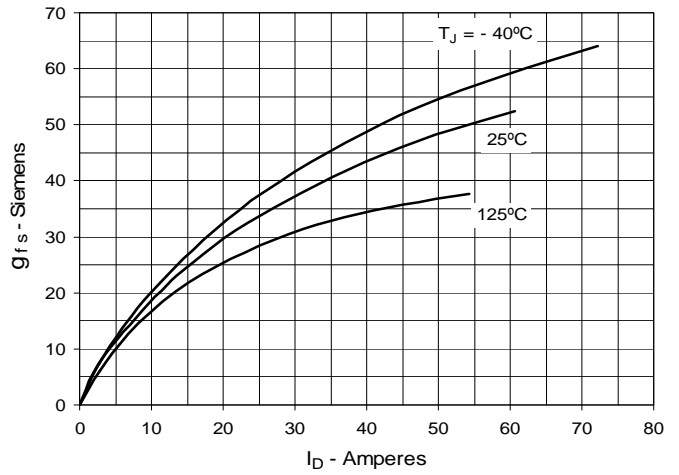
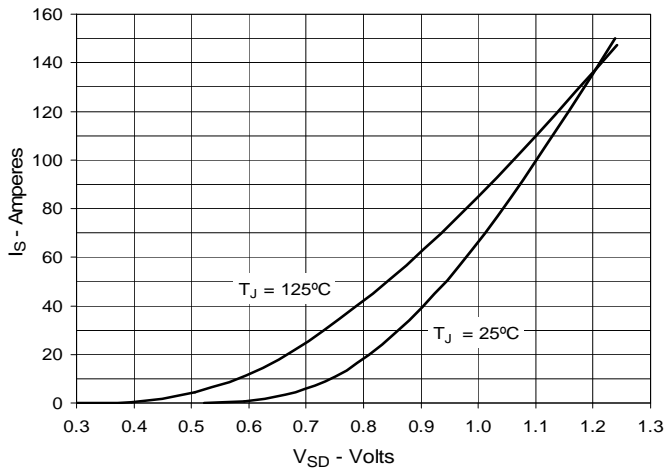
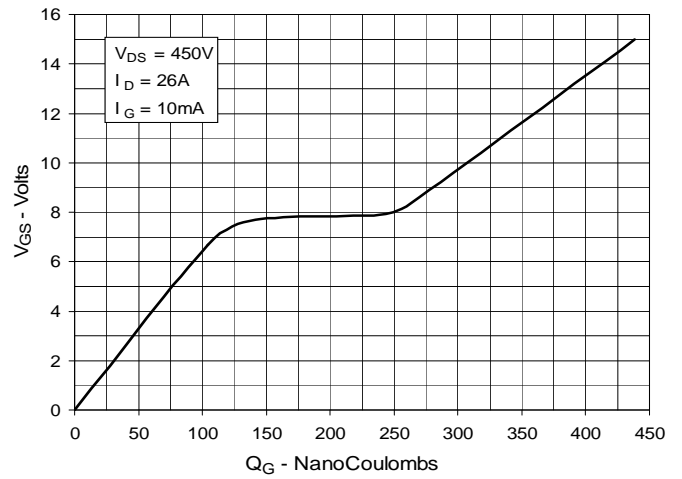
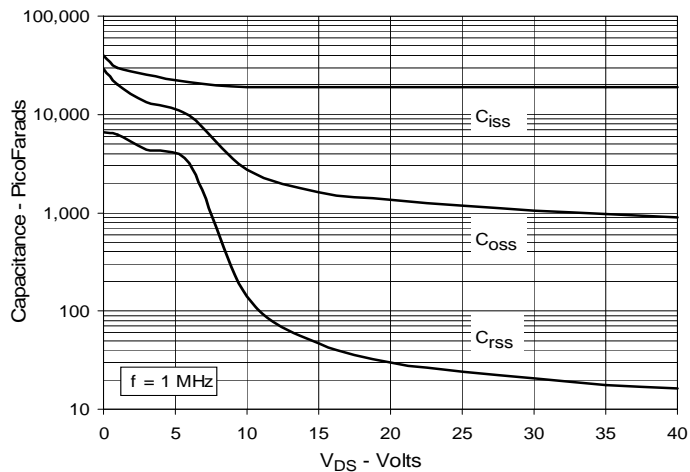
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 26\text{A}$ Value
vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 26\text{A}$ Value
vs. Drain Current**

**Fig. 6. Maximum Drain Current vs.
Case Temperature**


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance
